



2SD389

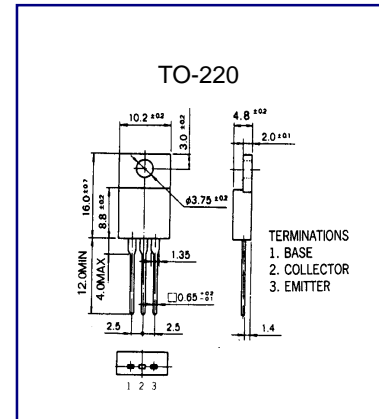
NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

- Complement to 2SB507

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CE0}	60	V
Emitter-Base voltage	V _{EB0}	7	V
Collector Current (DC)	I _C	4	A
Collector Dissipation ($T_c=25^\circ\text{C}$)	P _C	30	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-50~150	°C



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = 60V , I _E =0			100	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = 7V , I _C =0			100	μA
DC Current Gain	h _{FE1}	V _{CE} = 3V , I _C =1A		70		
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _C =2A , I _B =0.2A			1.0	V
Current Gain Bandwidth Product	f _T	V _{CE} = 5V , I _C =0.5A		18		MHZ